

# MOS INTEGRATED CIRCUIT $\mu PD434004AL$

# 4M-BIT CMOS FAST SRAM 1M-WORD BY 4-BIT

#### **Description**

The  $\mu$ PD434004AL is a high speed, low power, 4,194,304 bits (1,048,576 words by 4 bits) CMOS static RAM.

Operating supply voltage is 3.3 V  $\pm$  0.3 V.

The  $\mu\text{PD434004AL}$  is packaged in a 32-pin plastic SOJ.

#### **Features**

• 1,048,576 words by 4 bits organization

• Fast access time: 15, 17, 20 ns (MAX.)

• Output Enable input for easy application

• Single +3.3 V power supply

#### **Ordering Information**

Part number	Package	Access time	Supply currer	nt mA (MAX.)
		ns (MAX.)	At operating	At standby
μPD434004ALLE-A15	32-pin plastic SOJ	15	130	5
μPD434004ALLE-A17	(10.16 mm (400))	17	120	
μPD434004ALLE-A20		20	110	

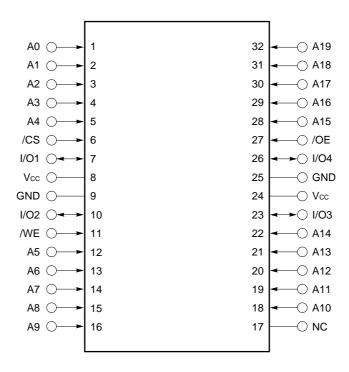
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Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

## ★ Pin Configuration (Marking Side)

/xxx indicates active low signal.

32-pin plastic SOJ (10.16 mm (400)) [  $\mu$ PD434004ALLE ]



A0 - A19 : Address Inputs

I/O1 - I/O4 : Data Inputs / Outputs

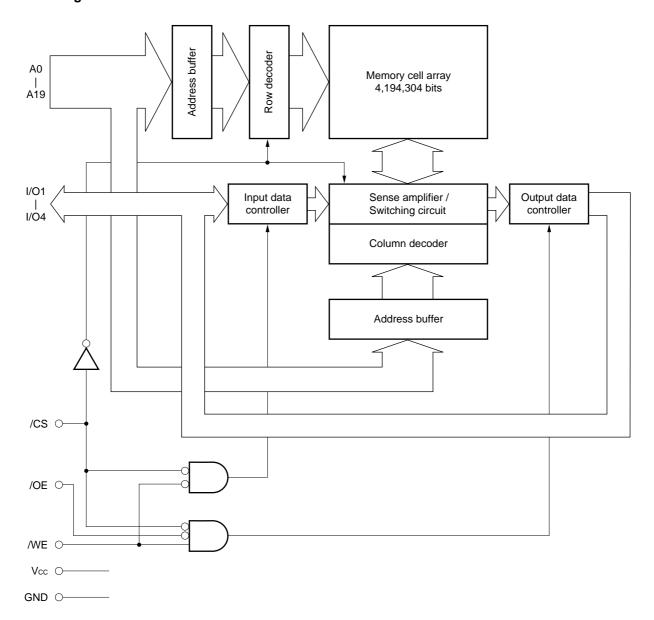
/CS : Chip Select
/WE : Write Enable
/OE : Output Enable
Vcc : Power supply
GND : Ground

NC : No connection

Remark Refer to Package Drawing for the 1-pin index mark.



## **Block Diagram**



**Truth Table** 

/CS	/OE	/WE	Mode	I/O	Supply current
Н	×	×	Not selected	High impedance	Isb
L	L	Н	Read	<b>D</b> оит	Icc
L	×	L	Write	Din	
L	Н	Н	Output disable	High impedance	

Remark ×: Don't care



## **Electrical Specifications**

## **Absolute Maximum Ratings**

Parameter	Symbol	Condition	Rating	Unit
Supply voltage	Vcc		-0.5 <sup>Note</sup> to +4.6	V
Input / Output voltage	VT		-0.5 <sup>Note</sup> to +4.6	V
Operating ambient temperature	TA		0 to 70	°C
Storage temperature	Tstg		-55 to +125	°C

Note -2.0 V (MIN.) (pulse width: 2 ns)

Caution Exposing the device to stress above those listed in Absolute Maximum Rating could cause permanent damage. The device is not meant to be operated under conditions outside the limits described in the operational section of this specification. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

## **Recommended Operating Conditions**

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Supply voltage	Vcc		3.0	3.3	3.6	V
High level input voltage	VIH		2.2		Vcc+0.3	٧
Low level input voltage	VIL		-0.3 Note		+0.8	٧
Operating ambient temperature	TA		0		70	°C

Note -2.0 V (MIN.) (pulse width: 2 ns)



## DC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit	
Input leakage current	lu	VIN = 0 V to Vcc		-2		+2	μΑ
Output leakage current	ILO	$V_{I/O} = 0 V \text{ to } V_{CC},$		-2		+2	μΑ
		/CS = VIH or /OE = VIH	or /WE = VIL				
Operating supply current	Icc	/CS = VIL,	Cycle time : 15 ns			130	mA
		I <sub>1</sub> /0 = 0 mA,	Cycle time : 17 ns			120	
		Minimum cycle time	Cycle time : 20 ns			110	
Standby supply current	Isa	/CS = VIH, VIN = VIH or	VIL			50	mA
	I <sub>SB1</sub>	/CS ≥ Vcc - 0.2 V,	/CS ≥ Vcc - 0.2 V,			5	
		$V_{\text{IN}} \leq 0.2 \; \text{V} \; \text{or} \; V_{\text{IN}} \geq V_{\text{CC}} - 0.2 \; \text{V}$					
High level output voltage	Vон	Iон = -4.0 mA	2.4			V	
Low level output voltage	Vol	IoL = +8.0 mA				0.4	V

Remark VIN: Input voltage

Vi/o: Input / Output voltage

## Capacitance (T<sub>A</sub> = 25 °C, f = 1 MHz)

Parameter	Symbol	Test condition	MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	VIN = 0 V			6	pF
Input / Output capacitance	Cı/o	V <sub>1/O</sub> = 0 V			10	pF

Remarks 1. VIN: Input voltage

Vi/o: Input / Output voltage

 $\pmb{2.}\ \ \, \text{These parameters are periodically sampled and not 100% tested.}$ 

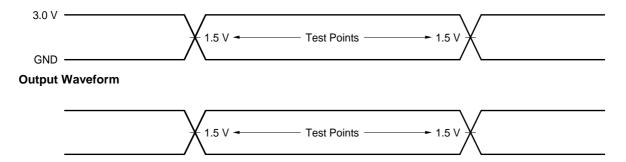
Data Sheet M12225EJ5V0DS00 5



#### **AC Characteristics (Recommended Operating Conditions Unless Otherwise Noted)**

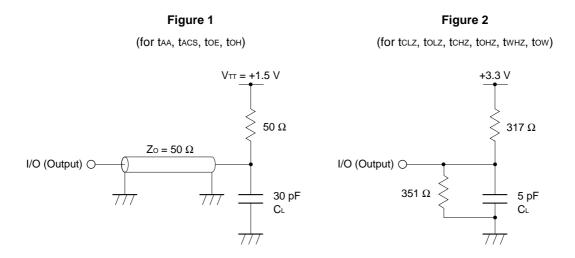
#### **AC Test Conditions**

## Input Waveform (Rise and Fall Time ≤ 3 ns)



## **Output Load**

AC characteristics directed with the note should be measured with the output load shown in **Figure 1** or **Figure 2**.



Remark CL includes capacitances of the probe and jig, and stray capacitances.



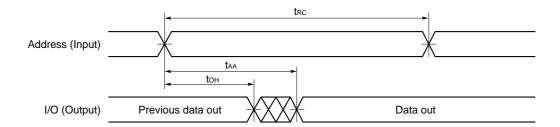
## **Read Cycle**

Parameter	Symbol	μPD434004AL-A15		μPD434004AL-A17		μPD434004AL-A20		Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Read cycle time	<b>t</b> RC	15		17		20		ns	
Address access time	taa		15		17		20	ns	1
/CS access time	tacs		15		17		20	ns	
/OE access time	toe		7		8		10	ns	
Output hold from address change	tон	3		3		3		ns	
/CS to output in low impedance	tclz	3		3		3		ns	2, 3
/OE to output in low impedance	tolz	0		0		0		ns	
/CS to output in high impedance	tснz		7		8		8	ns	
/OE to output hold in high impedance	tонz		7		8		8	ns	

Notes 1. See the output load shown in Figure 1.

- 2. Transition is measured at  $\pm$  200 mV from steady-state voltage with the output load shown in **Figure 2**.
- 3. These parameters are periodically sampled and not 100% tested.

## Read Cycle Timing Chart 1 (Address Access)

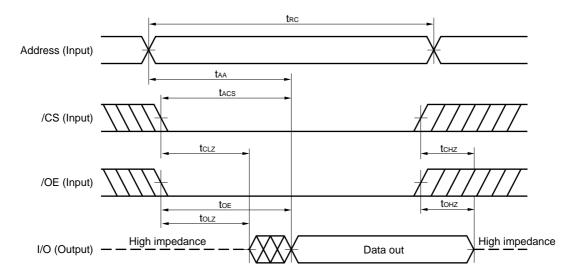


Remarks 1. In read cycle, /WE should be fixed to high level.

2. /CS = /OE = VIL



## Read Cycle Timing Chart 2 (/CS Access)



Caution Address valid prior to or coincident with /CS low level input.

**Remark** In read cycle, /WE should be fixed to high level.



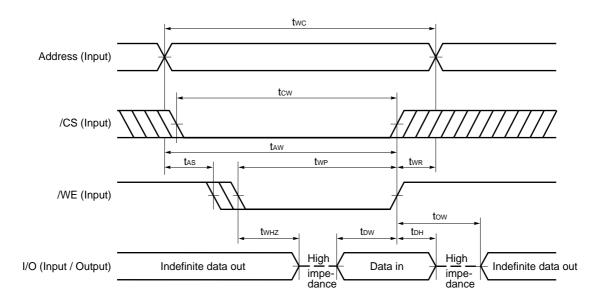
#### **Write Cycle**

Parameter	Symbol	μPD4340	04AL-A15	μPD4340	04AL-A17	μPD4340	04AL-A20	Unit	Notes
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Write cycle time	twc	15		17		20		ns	
/CS to end of write	tcw	10		11		12		ns	
Address valid to end of write	taw	10		11		12		ns	
Write pulse width	twp	10		11		12		ns	
Data valid to end of write	tow	7		8		9		ns	
Data hold time	tон	0		0		0		ns	
Address setup time	tas	0		0		0		ns	
Write recovery time	twr	1		1		1		ns	
/WE to output in high impedance	twnz		7		8		8	ns	1, 2
Output active from end of write	tow	3		3		3		ns	

**Notes 1.** Transition is measured at  $\pm$  200 mV from steady-state voltage with the output load shown in **Figure 2**.

2. These parameters are periodically sampled and not 100% tested.

## Write Cycle Timing Chart 1 (/WE Controlled)

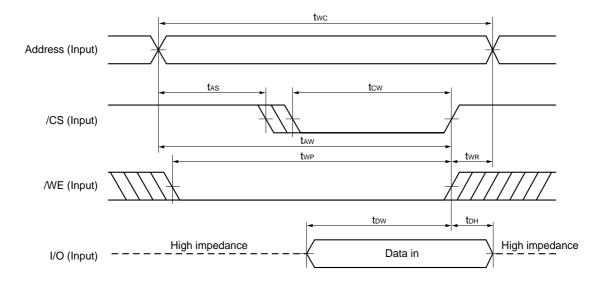


Caution /CS or /WE should be fixed to high level during address transition.

- Remarks 1. Write operation is done during the overlap time of a low level /CS and a low level /WE.
  - 2. During twHZ, I/O pins are in the output state, therefore the input signals must not be applied to the output.
  - 3. When /WE is at low level, the I/O pins are always high impedance. When /WE is at high level, read operation is executed. Therefore /OE should be at high level to make the I/O pins high impedance.



## Write Cycle Timing Chart 2 (/CS Controlled)

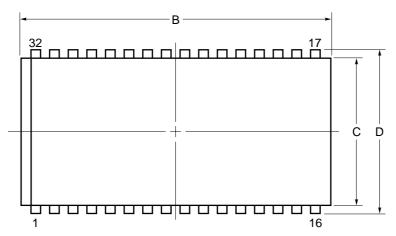


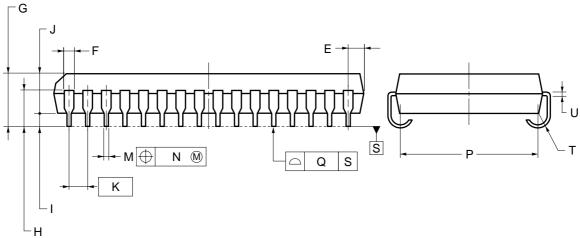
Caution /CS or /WE should be fixed to high level during address transition.

**Remark** Write operation is done during the overlap time of a low level /CS and a low level /WE.

## Package Drawing

# 32-PIN PLASTIC SOJ (10.16mm (400))





## NOTE

Each lead centerline is located within 0.12 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
В	21.26±0.2
С	10.16
D	11.18±0.2
E	1.005±0.1
F	0.74
G	3.5±0.2
Н	2.545±0.2
I	0.8 MIN.
J	2.6
K	1.27(T.P.)
М	0.40±0.10
N	0.12
Р	9.4±0.20
Q	0.1
T	R0.85
U	$0.20^{+0.10}_{-0.05}$

P32LE-400A-1



# **Recommended Soldering Conditions**

Please consult with our sales offices for soldering conditions of the  $\mu$ PD434004AL.

# **Type of Surface Mount Device**

 $\mu$ PD434004ALLE : 32-pin plastic SOJ (10.16 mm (400))

NEC  $\mu$ PD434004AL

[MEMO]

NEC  $\mu$ PD434004AL

[MEMO]



#### - NOTES FOR CMOS DEVICES -

#### 1 PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

#### ② HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

#### (3) STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

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